



# PJA3409

## 30V P-Channel Enhancement Mode MOSFET

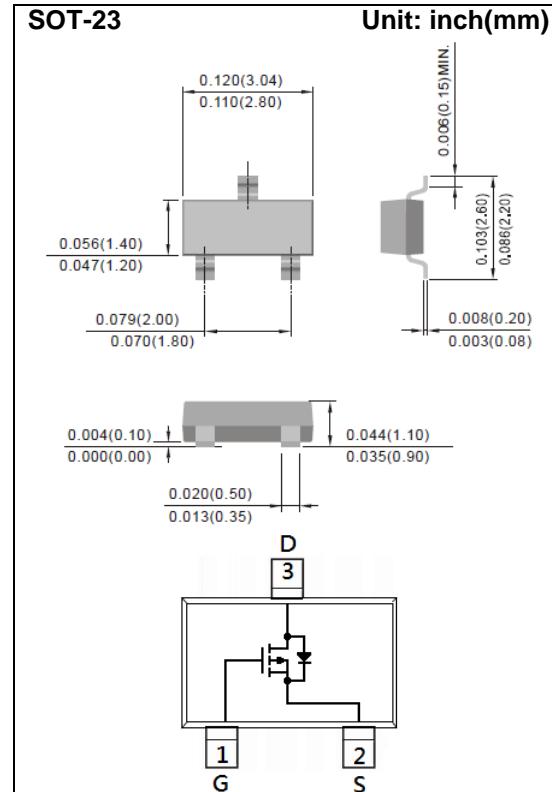
Voltage      -30 V      Current      -2.9A

### Features

- RDS(ON) , VGS@-10V, ID@-2.9A<110mΩ
- RDS(ON) , VGS@-4.5V, ID@-1.9A<150mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

### Mechanical Data

- Case: SOT-23 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams
- Marking: A09



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	+20	V
Continuous Drain Current		$I_D$	-2.9	A
Pulsed Drain Current		$I_{DM}$	-11.6	A
Power Dissipation	$T_a=25^\circ\text{C}$	$P_D$	1.25	W
	Derate above $25^\circ\text{C}$		10	mW/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	$^\circ\text{C}$
Typical Thermal resistance - Junction to Ambient	<sup>(Note 3)</sup>	$R_{\theta JA}$	100	$^\circ\text{C/W}$



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### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.31	-2.1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-2.9A$	-	92	110	$m\Omega$
		$V_{GS}=-4.5V, I_D=-1.9A$	-	120	150	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	-	-0.01	-1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	$\pm 10$	$\pm 100$	$nA$
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15V, I_D=-2.9A,$ $V_{GS}=-10V$ (Note 1,2)	-	9.8	-	$nC$
Gate-Source Charge	$Q_{gs}$		-	1.5	-	
Gate-Drain Charge	$Q_{gd}$		-	2.2	-	
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	396	-	$pF$
Output Capacitance	$C_{oss}$		-	47	-	
Reverse Transfer Capacitance	$C_{rss}$		-	36	-	
<b>Switching</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-2.9A,$ $V_{GS}=-10V,$ $R_G=6\Omega$ (Note 1,2)	-	5	-	$ns$
Turn-On Rise Time	$tr$		-	30	-	
Turn-Off Delay Time	$t_{d(off)}$		-	25	-	
Turn-Off Fall Time	$tf$		-	8	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_s$	---	-	-	-1.5	A
Diode Forward Voltage	$V_{SD}$	$I_s=-1.0A, V_{GS}=0V$		-0.77	-1.2	V

#### NOTES :

1. Pulse width $\leq 300\mu s$ , Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3.  $R_{QJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited



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## TYPICAL CHARACTERISTIC CURVES

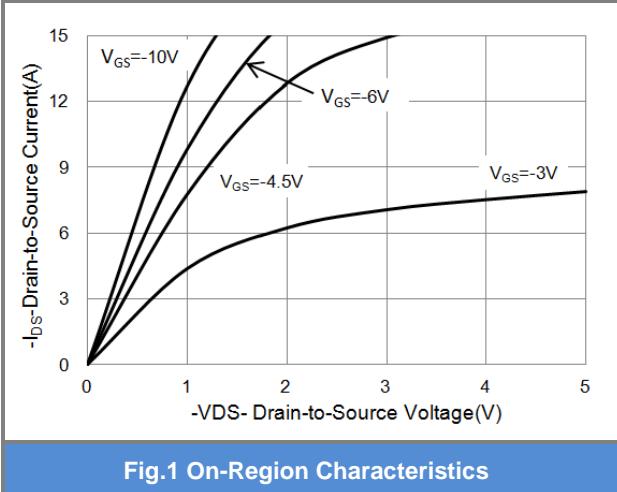


Fig.1 On-Region Characteristics

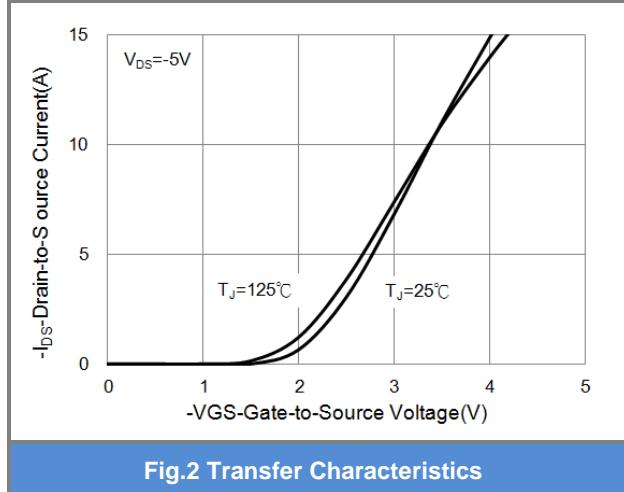


Fig.2 Transfer Characteristics

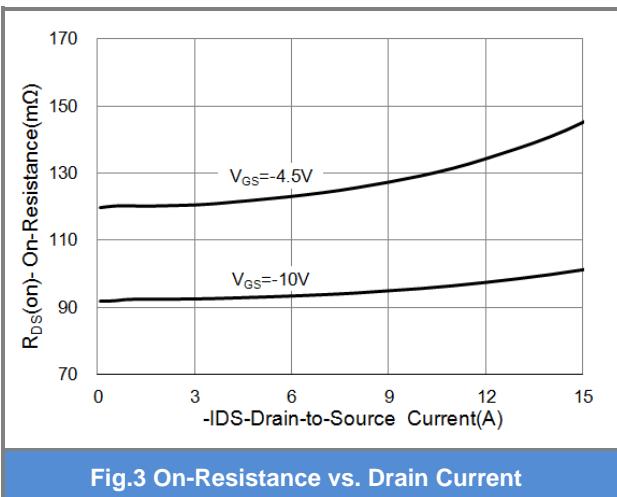


Fig.3 On-Resistance vs. Drain Current

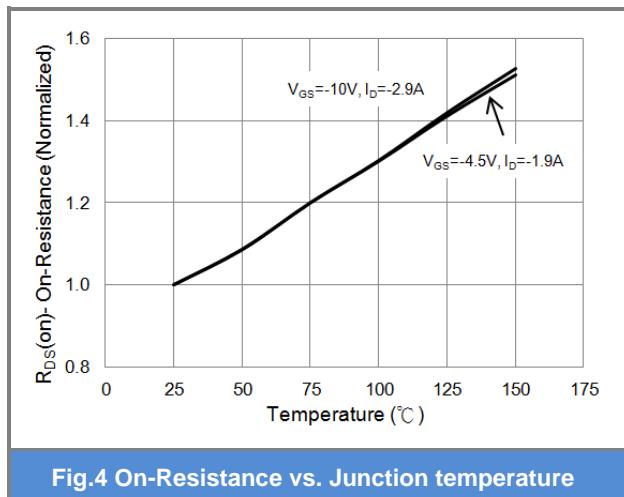


Fig.4 On-Resistance vs. Junction temperature

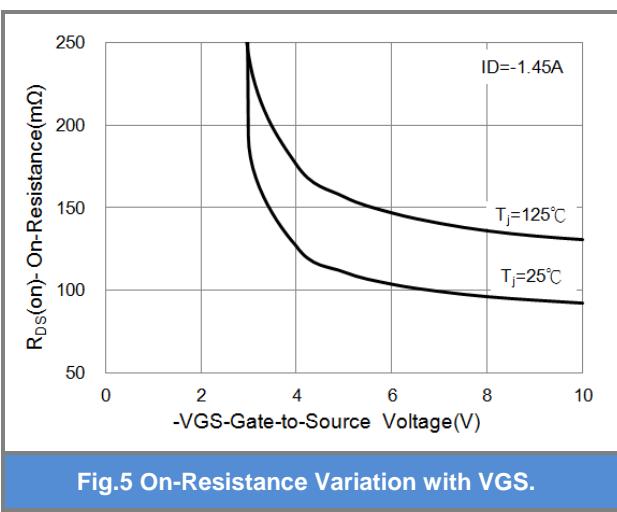


Fig.5 On-Resistance Variation with VGS.

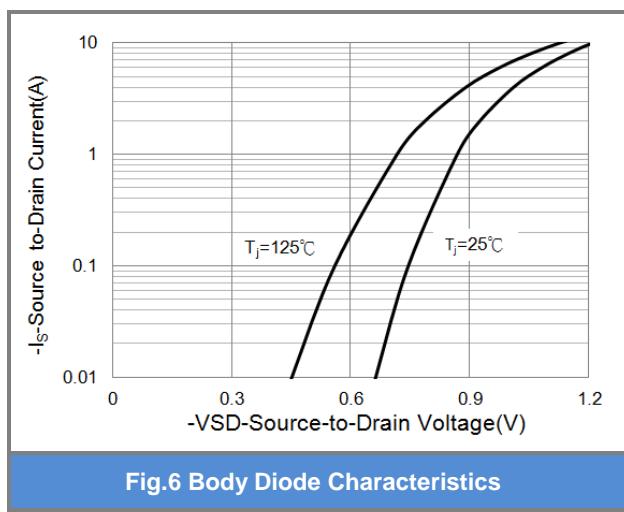


Fig.6 Body Diode Characteristics



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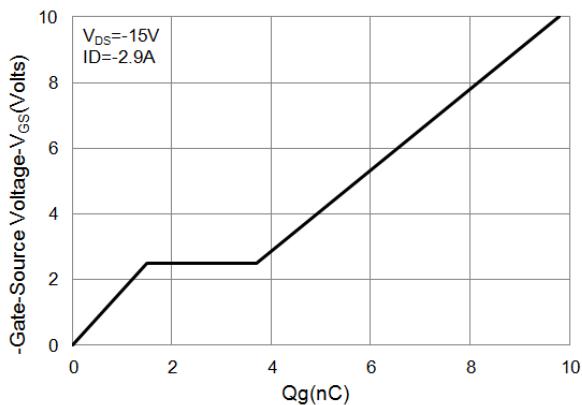


Fig.7 Gate-Charge Characteristics

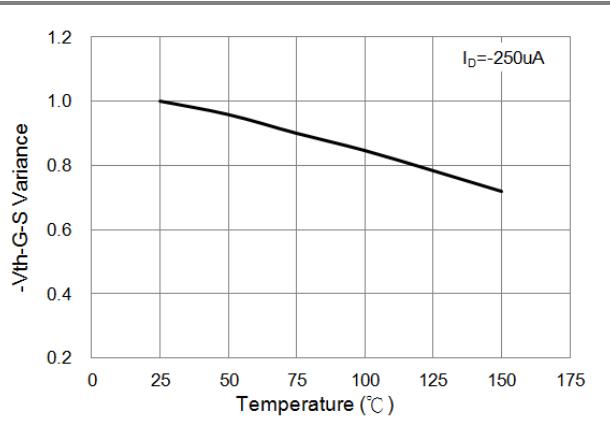


Fig.8 Threshold Voltage Variation with Temperature

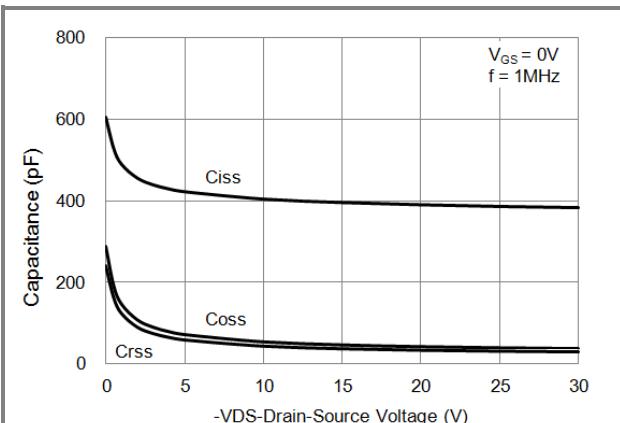


Fig.9 Capacitance vs. Drain-Source Voltage



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## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJA3409_R1_00001	SOT-23	3K pcs / 7" reel	A09	Halogen free
PJA3409_R2_00001	SOT-23	12K pcs / 13" reel	A09	Halogen free

## MOUNTING PAD LAYOUT

